

Double channel high-side driver with analog current sense for 24 V automotive applications

Features


PowerSSO-24

Description	Parameter	Value
Max. transient supply voltage	V_{CC}	58 V
Operating voltage range	V_{CC}	8 to 36 V
Typ. on-state resistance (per channel)	R_{ON}	50 mΩ
Current limitation (typ.)	I_{LIM}	34 A
Off-state supply current	I_S	2 μA



- AEC-Q100 qualified
- General
 - Very low standby current
 - 3.0 V CMOS compatible input
 - Optimized electromagnetic emission
 - Very low electromagnetic susceptibility
 - Compliant with European directive 2002/95/EC
 - Fault reset standby pin (FR_Stby)
- Diagnostic functions
 - Proportional load current sense
 - High current sense precision for wide range currents
 - Off-state openload detection
 - Output short to V_{CC} detection
 - Overload and short to ground latch-off
 - Thermal shutdown latch-off
 - Very low current sense leakage
- Protections
 - Undervoltage shutdown
 - Overvoltage clamp
 - Load current limitation
 - Self limiting of fast thermal transients
 - Protection against loss of ground and loss of V_{CC}
 - Thermal shutdown
 - Electrostatic discharge protection

Product status link	
VND5T050AK-E	
Product summary	
Order code	VND5T050AK-E
Package	PowerSSO-24
Packing	Tube
Order code	VND5T050AKTR-E
Package	PowerSSO-24
Packing	Tape and reel

Applications

- All types of resistive, inductive and capacitive loads

Description

The VND5T050AK-E is a monolithic device made using STMicroelectronics VIPower technology, intended for driving resistive or inductive loads with one side connected to the ground. Active V_{CC} pin voltage clamp protects the device against low energy spikes.

The device integrates an analog current sense, which delivers a current proportional to the load current.

Fault conditions such as overload, overtemperature, or short to V_{CC} are reported via the current sense pin.

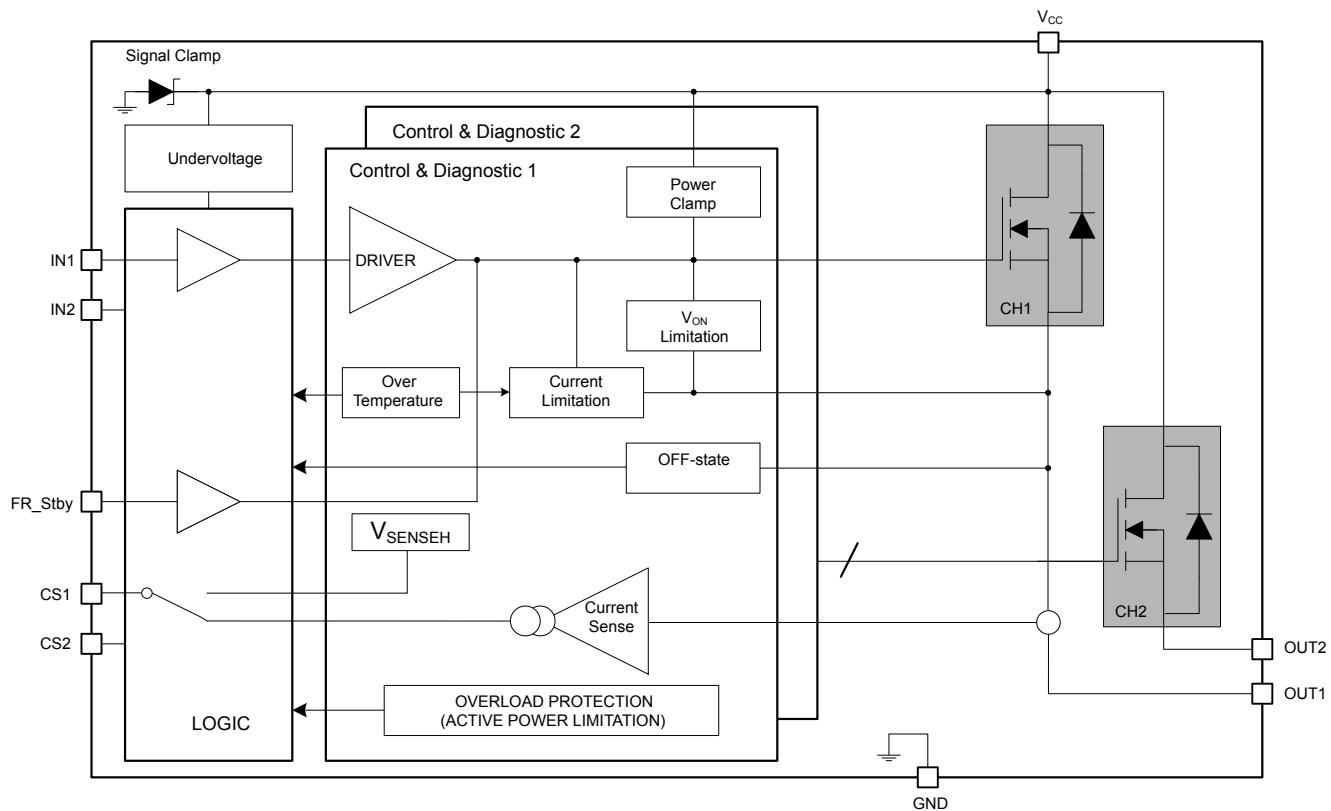
Output current limitation protects the device in overload conditions. The device latches off in case of overload or thermal shutdown.

The device is reset by a low level pass on the fault reset standby pin.

A permanent low level on the inputs and on the fault reset standby pins disables all outputs and sets the device in standby mode.

1 Block diagram and pin description

Figure 1. Block diagram

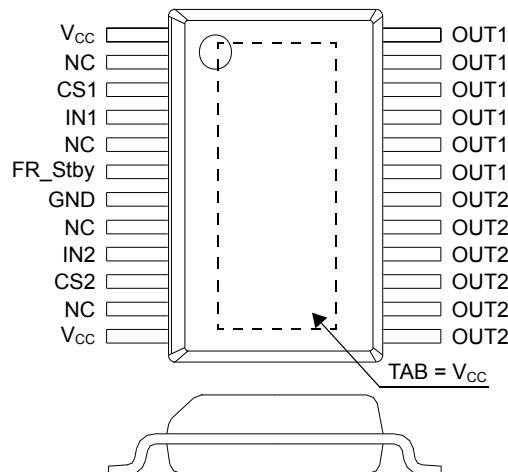


GAPGCFT00643

Table 1. Pin function

Name	Function
V _{CC}	Battery connection.
OUT1, 2	Power outputs.
GND	Ground connection.
IN1, 2	Voltage controlled input pins with hysteresis, CMOS compatible. They control output switch state.
CS1, 2	Analog current sense pins, they deliver a current proportional to the load current.
FR_Stby	In case of latch-off for overtemperature/overcurrent condition, a low pulse on the FR_Stby pin is needed to reset the channel. The device enters in standby mode if all inputs and the FR_Stby pin are low.

Figure 2. Configuration diagram PowerSSO-24 (top view)



GAPGCFT00435

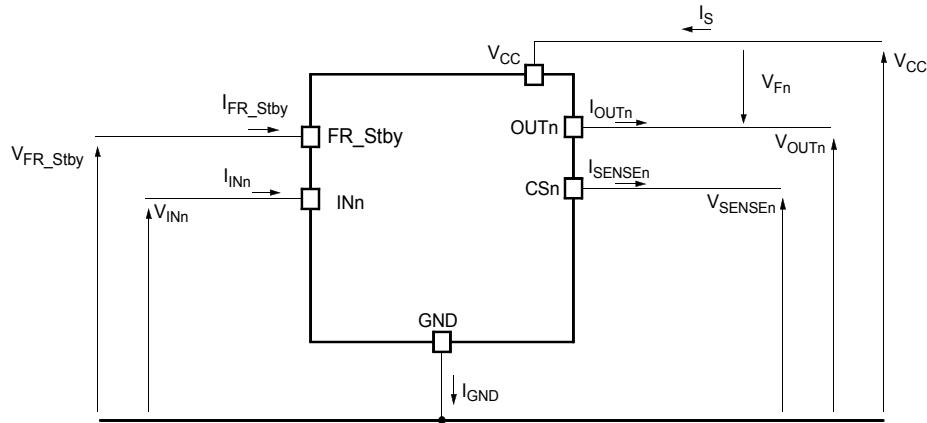
Table 2. Suggested connections for unused and not connected pins

Connection/pin	CurrentSense	NC	Output	Input	FR_Stby
Floating	Not allowed	X ⁽¹⁾	X	X	X
To ground	Through 10 kΩ resistor	X	Not allowed	Through 10 kΩ resistor	Through 10 kΩ resistor

1. X: do not care.

2 Electrical specification

Figure 3. Current and voltage conventions



GAPGCFT00195_v2

2.1 Absolute maximum ratings

Stressing the device above the ratings listed in the Table 3 may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to the conditions reported in this section for extended periods may affect device reliability.

Table 3. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CC}	DC supply voltage	58	V
-V _{CC}	Reverse DC supply voltage	0.3	V
-I _{GND}	DC reverse ground pin current	200	mA
I _{OUT}	DC output current	Internally limited	A
-I _{OUT}	Reverse DC output current	30	A
I _{IN}	DC input current	-1 to 10	mA
I _{FR_Stby}	Fault reset standby DC input current	-1 to 1.5	mA
-I _{CSENSE}	DC reverse CS pin current	200	mA
V _{CSENSE}	Current sense maximum voltage	(V _{CC} - 58) to V _{CC}	V
E _{MAX}	Maximum switching energy (L = 50 mH; V _{BAT} = 32 V; T _{Jstart} = 150 °C; I _{OUT} = 2 A)	210	mJ
L _{smax}	Maximum stray inductance in short circuit condition R _L = 300 mΩ, V _{BAT} = 32 V, T _{Jstart} = 150 °C, I _{OUT} = I _{limH} (max.)	40	µH
V _{ESD}	Electrostatic discharge (human body model: R = 1.5 kΩ, C = 100 pF)	IN1, 2	4000
		CS1, 2	2000
		FR_Stby	4000
		OUT1, 2	5000
		V _{CC}	5000
V _{ESD}	Charge device model (CDM-AEC-Q100-011)	750	V

Symbol	Parameter	Value	Unit
T _J	Junction operating temperature	-40 to 150	°C
T _{stg}	Storage temperature	-55 to 150	°C

2.2 Thermal data

Table 4. Thermal data

Symbol	Parameter	Value	Unit
R _{thJC}	Thermal resistance, junction-to-case (with one channel ON)	2.4	°C/W
R _{thJA}	Thermal resistance, junction-to-ambient	See Figure 27	°C/W

2.3 Electrical characteristics

8 V < V_{CC} < 36 V, -40 °C < T_J < 150 °C, unless otherwise specified.

Table 5. Power section

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{CC}	Operating supply voltage		8	24	36	V
V _{USD}	Undervoltage shutdown			3.5	5	V
V _{USDhyst}	Undervoltage shutdown hysteresis			0.5		V
R _{ON}	On-state resistance ⁽¹⁾	I _{OUT} = 2 A, T _J = 25 °C		50		mΩ
		I _{OUT} = 2 A, T _J = 150 °C			100	
V _{clamp}	Clamp voltage	I _S = 20 mA	58	64	70	V
I _S	Supply current	Off-state, V _{CC} = 24 V, T _J = 25 °C, V _{IN} = V _{OUT} = V _{SENSE} = 0 V, V _{FR_Sby} = 0 V		2 ⁽²⁾	5 ⁽²⁾	μA
		On-state, V _{CC} = 24 V, V _{IN} = 5 V, I _{OUT} = 0 A		4.2	6	mA
I _{L(off)}	Off-state output current	V _{IN} = V _{OUT} = 0 V, V _{CC} = 24 V, T _J = 25 °C	0	0.01	3	μA
		V _{IN} = V _{OUT} = 0 V, V _{CC} = 24 V, T _J = 125 °C	0		5	
V _F	Output - V _{CC} diode voltage	-I _{OUT} = 2 A, T _J = 150 °C			0.7	V

1. For each channel.

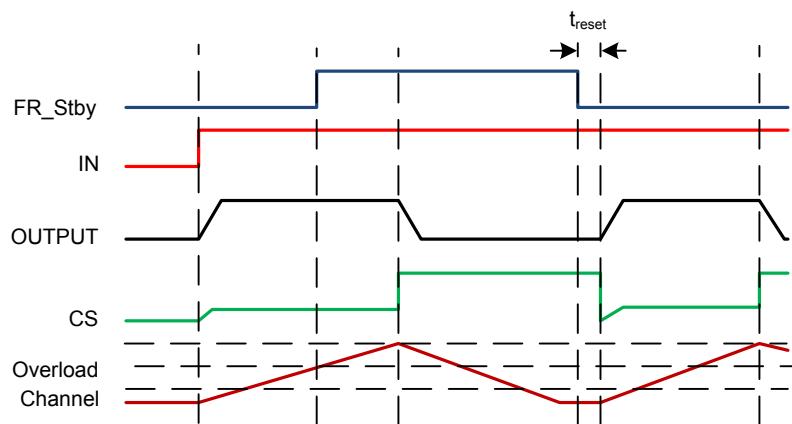
2. Power MOSFET leakage included.

Table 6. Switching ($V_{CC} = 24$ V, $T_J = 25$ °C)

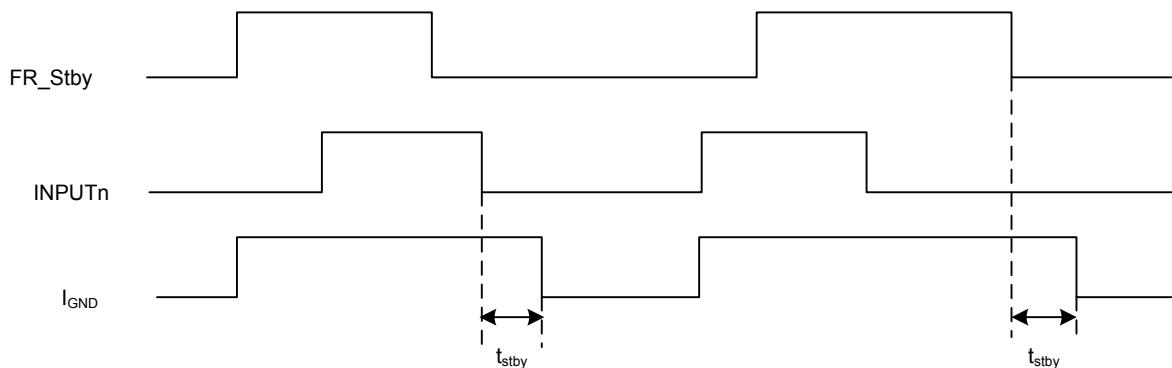
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$R_L = 12 \Omega$		30		μs
$t_{d(off)}$	Turn-off delay time	$R_L = 12 \Omega$		40		μs
$(dV_{OUT}/dt)_{(on)}$	Turn-on voltage slope	$R_L = 12 \Omega$		0.7		V/μs
$(dV_{OUT}/dt)_{(off)}$	Turn-off voltage slope	$R_L = 12 \Omega$		0.8		V/μs
W_{ON}	Switching energy losses during t_{won}	$R_L = 12 \Omega$		0.5		mJ
W_{OFF}	Switching energy losses during t_{woff}	$R_L = 12 \Omega$		0.3		mJ

Table 7. Logic inputs

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{IL}	Input low level voltage				0.9	V
I_{IL}	Low level input current	$V_{IN} = 0.9$ V	1			μA
V_{IH}	Input high level voltage		2.1			V
I_{IH}	High level input current	$V_{IN} = 2.1$ V			10	μA
$V_{I(hyst)}$	Input hysteresis voltage		0.25			V
V_{ICL}	Input clamp voltage	$I_{IN} = 1$ mA	5.5		7	V
		$I_{IN} = -1$ mA		-0.7		
$V_{FR_Stby_L}$	Fault_reset_standby low level voltage				0.9	V
$I_{FR_Stby_L}$	Low level fault_reset_standby current	$V_{FR_Stby} = 0.9$ V	1			μA
$V_{FR_Stby_H}$	Fault_reset_standby high level voltage		2.1			V
$I_{FR_Stby_H}$	High level fault_reset_standby current	$V_{FR_Stby} = 2.1$ V			10	μA
$V_{FR_Stby(hyst)}$	Fault_reset_standby hysteresis voltage		0.25			V
$V_{FR_Stby_CL}$	Fault_reset_standby clamp voltage	$I_{FR_Stby} = 15$ mA ($t < 10$ ms)	11		15	V
		$I_{FR_Stby} = -1$ mA		-0.7		V
t_{reset}	Overload latch-off reset time	See Figure 4	2		24	μs
t_{stby}	Standby delay	See Figure 5	120		1200	μs

Figure 4. t_{reset} definition


GAPGCFT000112

Figure 5. t_{stby} definition


GAPGCFT000111_v2

Table 8. Protections and diagnostics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{limH}	DC short circuit current	$V_{CC} = 24 \text{ V}$	24	34	46	A
		$5 \text{ V} < V_{CC} < 36 \text{ V}$			46	
I_{limL}	Short circuit current during thermal cycling	$V_{CC} = 24 \text{ V}, T_R < T_J < T_{TSD}$		8.5		A
T_{TSD}	Shutdown temperature		150	175	200	°C
T_R	Reset temperature		$T_{RS} + 1$	$T_{RS} + 5$		°C
T_{RS}	Thermal reset of status		135			°C
T_{HYST}	Thermal hysteresis ($T_{TSD} - T_R$)			7		°C
V_{DEMAG}	Turn-off output voltage clamp	$I_{OUT} = 2 \text{ A}, V_{IN} = 0 \text{ V}, L = 6 \text{ mH}$	$V_{CC} - 58$	$V_{CC} - 64$	$V_{CC} - 70$	V
V_{ON}	Output voltage drop limitation	$I_{OUT} = 100 \text{ mA}, T_J = -40 \text{ °C} \text{ to } 150 \text{ °C}$		25		mV

Table 9. Current sense ($8 \text{ V} < V_{CC} < 36 \text{ V}$)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
K_{OL}	I_{OUT}/I_{SENSE}	$I_{OUT} = 10 \text{ mA}, V_{SENSE} = 0.5 \text{ V}, T_J = -40 \text{ }^\circ\text{C to } 150 \text{ }^\circ\text{C}$	564	2800	5563	
		$I_{OUT} = 10 \text{ mA}, V_{SENSE} = 0.5 \text{ V}, T_J = 25 \text{ }^\circ\text{C to } 150 \text{ }^\circ\text{C}$	972		4895	
K_{LED}	I_{OUT}/I_{SENSE}	$I_{OUT} = 50 \text{ mA}, V_{SENSE} = 0.5 \text{ V}, T_J = -40 \text{ }^\circ\text{C to } 150 \text{ }^\circ\text{C}$	1193	2650	4268	
		$I_{OUT} = 50 \text{ mA}, V_{SENSE} = 0.5 \text{ V}, T_J = 25 \text{ }^\circ\text{C to } 150 \text{ }^\circ\text{C}$	1416		3958	
$dK_{LED}/K_{LEDTOT}^{(1)}$	Current sense ratio drift	$I_{OUT} = 12 \text{ mA to } 60 \text{ mA}, I_{CAL} = 35 \text{ mA}, V_{SENSE} = 0.5 \text{ V}$	-35		35	%
K_0	I_{OUT}/I_{SENSE}	$I_{OUT} = 100 \text{ mA}, V_{SENSE} = 0.5 \text{ V}, T_J = -40 \text{ }^\circ\text{C to } 150 \text{ }^\circ\text{C}$	1409	2540	3726	
$dK_0/K_0^{(1)}$	Current sense ratio drift	$I_{OUT} = 100 \text{ mA}, V_{SENSE} = 0.5 \text{ V}, T_J = -40 \text{ }^\circ\text{C to } 150 \text{ }^\circ\text{C}$	-20		20	%
K_1	I_{OUT}/I_{SENSE}	$I_{OUT} = 0.7 \text{ A}, V_{SENSE} = 2 \text{ V}, T_J = -40 \text{ }^\circ\text{C to } 150 \text{ }^\circ\text{C}$	1597	2190	2764	
$dK_1/K_1^{(1)}$	Current sense ratio drift	$I_{OUT} = 0.7 \text{ A}, V_{SENSE} = 2 \text{ V}, T_J = -40 \text{ }^\circ\text{C to } 150 \text{ }^\circ\text{C}$	-15		15	%
K_2	I_{OUT}/I_{SENSE}	$I_{OUT} = 2 \text{ A}, V_{SENSE} = 2 \text{ V}, T_J = -40 \text{ }^\circ\text{C to } 150 \text{ }^\circ\text{C}$	1850	2190	2550	
$dK_2/K_2^{(1)}$	Current sense ratio drift	$I_{OUT} = 2 \text{ A}, V_{SENSE} = 2 \text{ V}, T_J = -40 \text{ }^\circ\text{C to } 150 \text{ }^\circ\text{C}$	-10		10	%
K_3	I_{OUT}/I_{SENSE}	$I_{OUT} = 8 \text{ A}, V_{SENSE} = 4 \text{ V}, T_J = -40 \text{ }^\circ\text{C to } 150 \text{ }^\circ\text{C}$	2050	2190	2280	
$dK_3/K_3^{(1)}$	Current sense ratio drift	$I_{OUT} = 8 \text{ A}, V_{SENSE} = 4 \text{ V}, T_J = -40 \text{ }^\circ\text{C to } 150 \text{ }^\circ\text{C}$	-3		3	%
I_{SENSE0}	Analog sense leakage current	$I_{OUT} = 0 \text{ A}, V_{SENSE} = 0 \text{ V}, V_{IN} = 0 \text{ V}, T_J = -40 \text{ }^\circ\text{C to } 150 \text{ }^\circ\text{C}$	0		1	μA
		$I_{OUT} = 0 \text{ A}, V_{SENSE} = 0 \text{ V}, V_{IN} = 5 \text{ V}, T_J = -40 \text{ }^\circ\text{C to } 150 \text{ }^\circ\text{C}$	0		2	
V_{SENSE}	Max analog sense output voltage	$I_{OUT} = 8 \text{ A}, R_{SENSE} = 3.9 \text{ k}\Omega$	5			V
V_{SENSEH}	Analog sense output voltage in fault condition ⁽²⁾	$V_{CC} = 24 \text{ V}, R_{SENSE} = 3.9 \text{ k}\Omega$	7.5	8.5	9.5	V
I_{SENSEH}	Analog sense output current in fault condition ⁽²⁾	$V_{CC} = 24 \text{ V}, V_{SENSE} = 5 \text{ V}$	4.9	7	12	mA
$t_{DSENSE2H}$	Delay response time from rising edge of INPUT pins	$V_{SENSE} < 4 \text{ V}, 0.15 \text{ A} < I_{OUT} < 8 \text{ A}, I_{SENSE} = 90\% \text{ of } I_{SENSEMAX}, (\text{see Figure 6})$		150	300	μs
$\Delta t_{DSENSE2H}$	Delay response time between rising edge of output current and rising edge of current sense	$V_{SENSE} < 4 \text{ V}, I_{SENSE} = 90\% \text{ of } I_{SENSEMAX}, I_{OUT} = 90\% \text{ of } I_{OUTMAX}, I_{OUTMAX} = 2 \text{ A} (\text{see Figure 10})$			250	μs

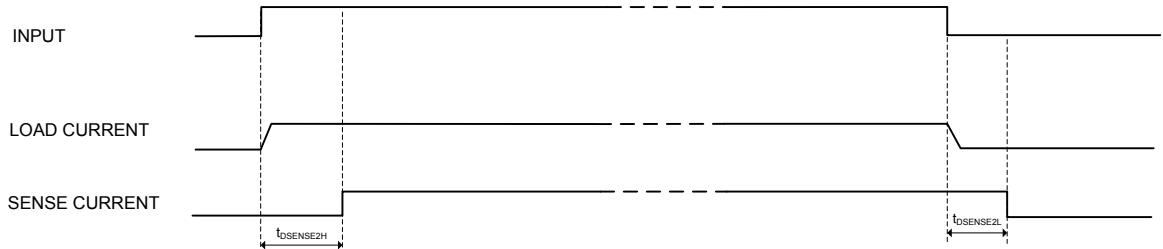
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{DSENSE2L}$	Delay response time from falling edge of INPUT pins	$V_{SENSE} < 4 \text{ V}$, $0.15 \text{ A} < I_{OUT} < 8 \text{ A}$, $I_{SENSE} = 10\% \text{ of } I_{SENSEMAX}$ (see Figure 6)		5	20	μs

1. Specified by design, not tested in production.
2. Fault condition includes: power limitation, overtemperature and openload in off-state condition.

Table 10. Openload detection ($V_{FR_Stby} = 5 \text{ V}$)

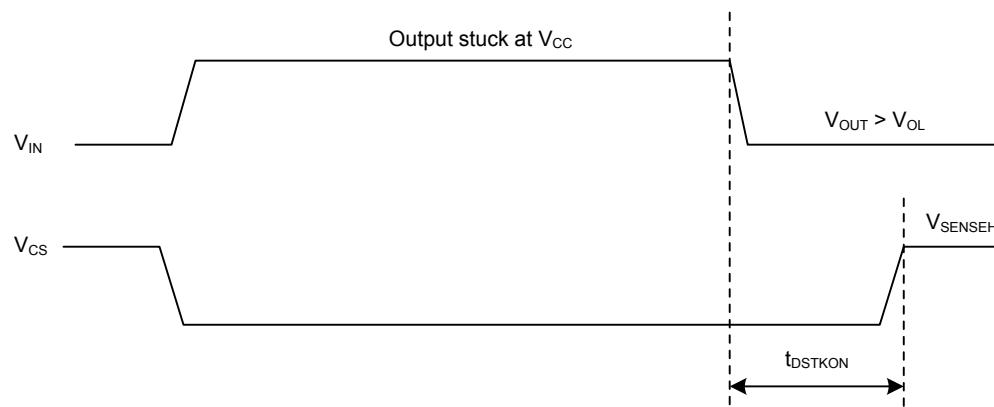
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{OL}	Openload off-state voltage detection threshold	$V_{IN} = 0 \text{ V}$, $8 \text{ V} < V_{CC} < 36 \text{ V}$	2	-	4	V
t_{DSTKON}	Output short circuit to V_{CC} detection delay at turn off	See Figure 7	180	-	1800	μs
$I_{L(off2)}$	Off-state output current at $V_{OUT} = 4 \text{ V}$	$V_{IN} = 0 \text{ V}$, $V_{SENSE} = 0 \text{ V}$, V_{OUT} rising from 0 V to 4 V	-120	-	0	μA
t_{d_vol}	Delay response from output rising edge to V_{SENSE} rising edge in openload	$V_{OUT} = 4 \text{ V}$, $V_{IN} = 0 \text{ V}$, $V_{SENSE} = 90\% \text{ of } V_{SENSEH}$, $R_{SENSE} = 3.9 \text{ k}\Omega$		-	20	μs
t_{DFRSTK_ON}	Output short circuit to V_{CC} detection delay at FR_Stby activation	Input1, 2 = low (see Figure 9)		-	50	μs

Figure 6. Current sense delay characteristics

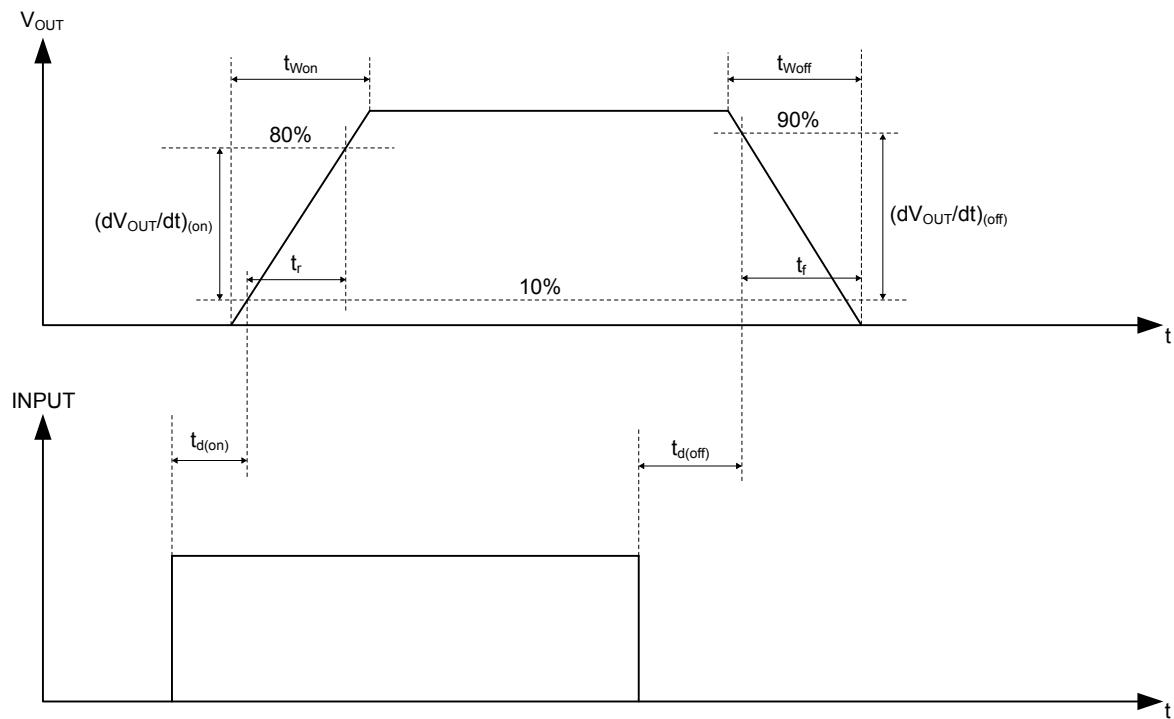


GAPGCFT000117

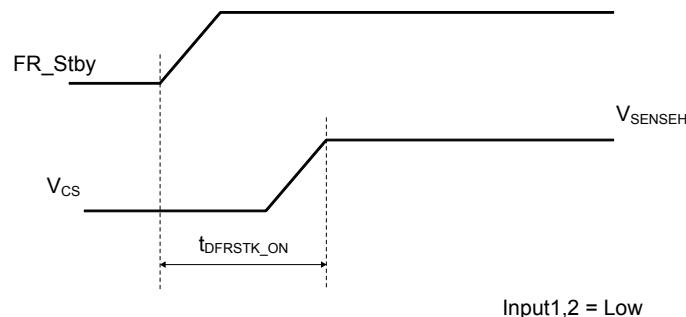
Figure 7. Openload off-state delay timing



GAPGCFT000113

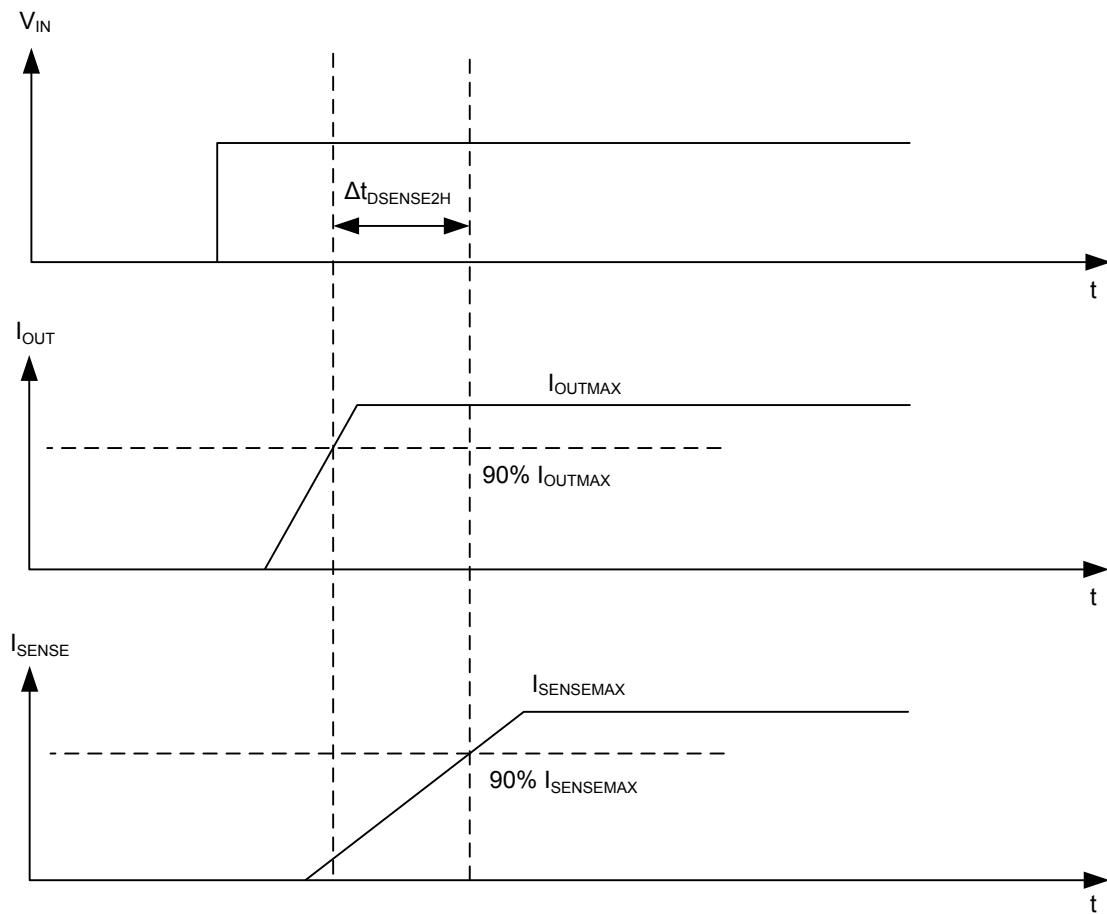
Figure 8. Switching characteristics


GAPGCFT000114

Figure 9. Output stuck to V_{CC} detection delay time at FR_Stby activation


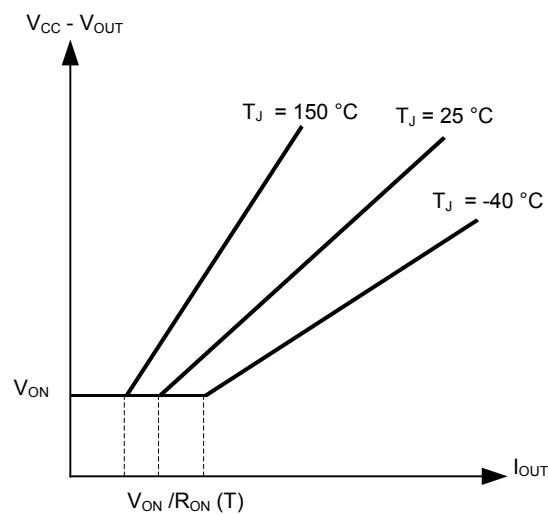
GAPGCFT00038_v2

Figure 10. Delay response time between rising edge of output current and rising edge of current sense



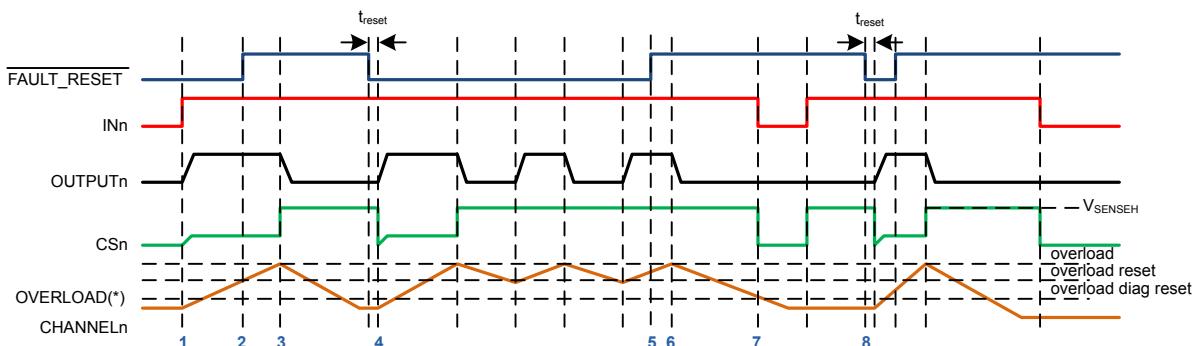
GAPGCFT000115

Figure 11. Output voltage drop limitation



AG00074V1

Figure 12. Device behavior in overload condition



- 1: OUTPUTn and CSn controlled by INn
 - 2: FAULT_RESET from '0' to '1' → no action on CSn pin
 - 3: overload latch-off. INn high → CSn high
 - 4: FAULT_RESET low AND Temp channeln < overload_reset → overload latch reset after t_{reset}
 - 4 to 5: FAULT_RESET low AND INn high → thermal cycling, CSn high
 - 5: FAULT_RESET high → latch-off reset disabled
 - 6 to 7: overload event and FAULT_RESET high → latch-off, no thermal cycling
 - 7 to 8: overload diagnostic disabled/enabled by the input
 - 8: overload latch-off reset by FAULT_RESET
- (*) OVERLOAD = thermal shutdown OR power limitation

GAPGCFT000116_v2

Table 11. Truth table

Conditions	Fault reset standby	Input	Output	Sense
Standby	L	L	L	0
Normal operation	X	L	L	0
	X	H	H	Nominal
Overload	X	L	L	0
	X	H	H	> Nominal
Overtemperature/short to ground	X	L	L	0
	L	H	Cycling	V_{SENSEH}
	H	H	Latched	V_{SENSEH}
Undervoltage	X	X	L	0
Short to V_{BAT}	L	L	H	0
	H	L	H	V_{SENSEH}
	X	H	H	< Nominal
Openload off-state (with pull-up)	L	L	H	0
	H	L	H	V_{SENSEH}
	X	H	H	0
Negative output voltage clamp	X	L	Negative	0

Table 12. Electrical transient requirements (part 1)

ISO 7637-2: 2004 (E) Test pulse	Test levels ⁽¹⁾		Number of pulses or test times	Burst cycle/pulse repetition time		Delays and impedance
	III	IV				
1	-450 V	-600 V	5000 pulses	0.5 s	5 s	1 ms, 50 Ω
2a	37 V	50 V	5000 pulses	0.2 s	5 s	50 μs, 2 Ω
3a	- 150 V	- 200 V	1 h	90 ms	100 ms	0.1 μs, 50 Ω
3b	+ 150 V	+ 200 V	1 h	90 ms	100 ms	0.1 μs, 50 Ω
4	- 12 V	- 16 V	1 pulse			100 ms, 0.01 Ω
5b ⁽²⁾	+ 123 V	+ 174 V	1 pulse			350 ms, 1 Ω

1. The above test levels must be considered referred to $V_{CC} = 24.5$ V except for pulse 5b.

2. Valid in case of external load dump clamp: 58 V maximum referred to ground.

Table 13. Electrical transient requirements (part 2)

ISO 7637-2: 2004 (E) Test pulse	Test level results ⁽¹⁾	
	III	IV
1	C	C
2a	C	C
3a	C	C
3b ⁽²⁾	E	E
3b ⁽³⁾	C	C
4	C	C
5b ⁽⁴⁾	C	C

1. In order to guarantee the ISO transient classes a minimum 10 kΩ protection resistors are needed on logic pins.

2. Without capacitor between V_{CC} and GND.

3. With 10 nF between V_{CC} and GND.

4. External load dump clamp, 58 V maximum, referred to ground.

Table 14. Electrical transient requirements (part 3)

Class	Contents
C	All functions of the device are performed as designed after exposure to disturbance.
E	One or more functions of the device are not performed as designed after exposure to disturbance and cannot be returned to proper operation without replacing the device.

2.4 Electrical characteristics (curves)

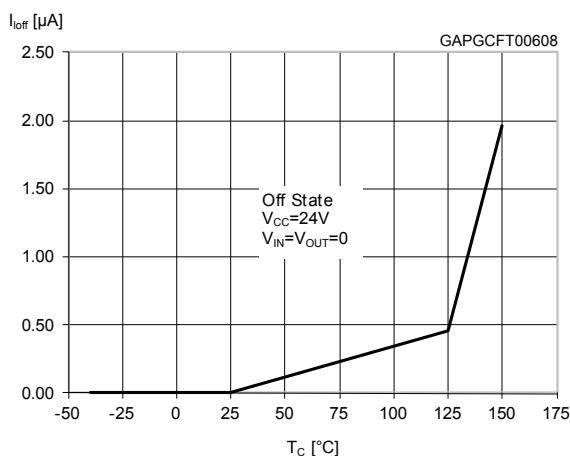
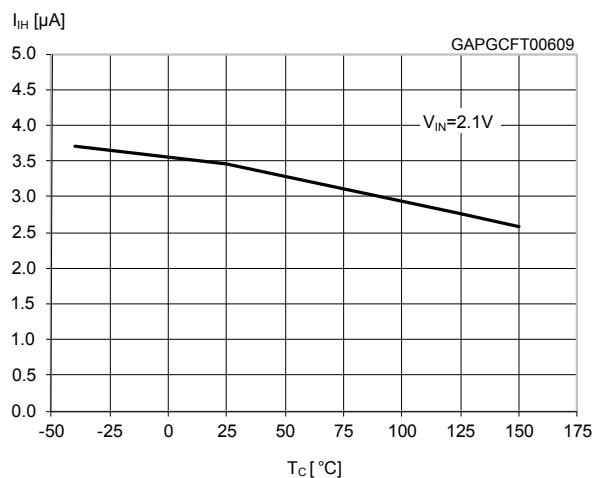
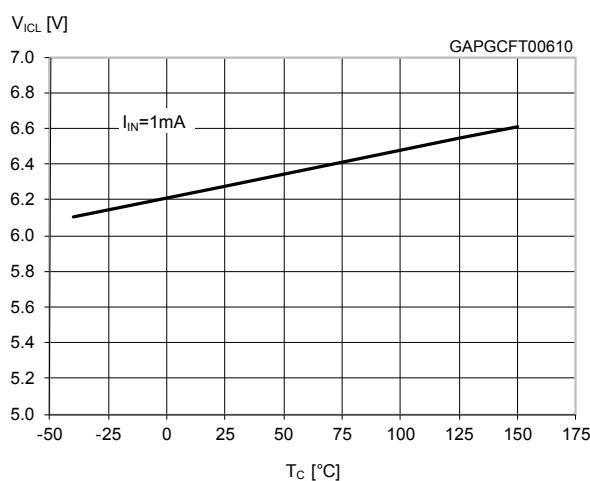
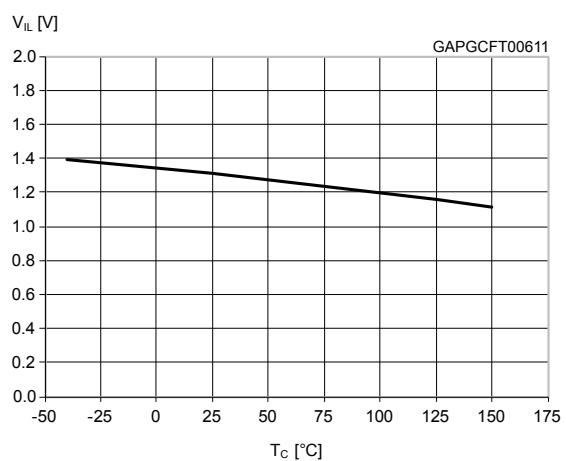
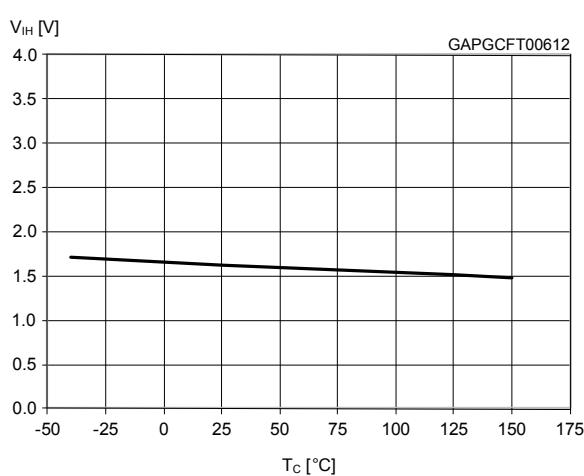
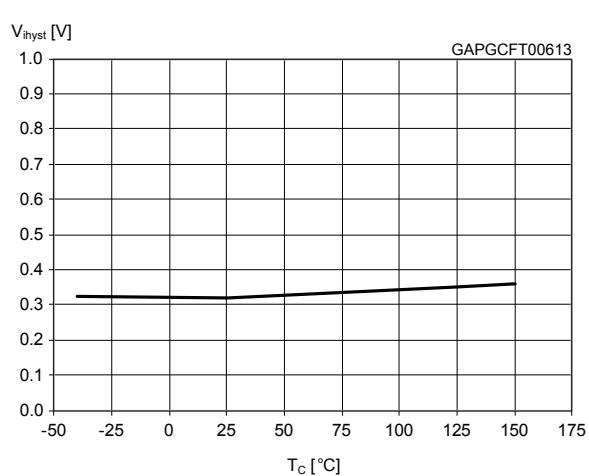
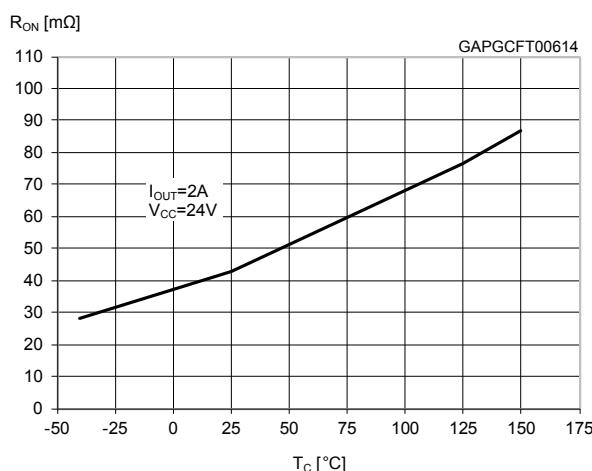
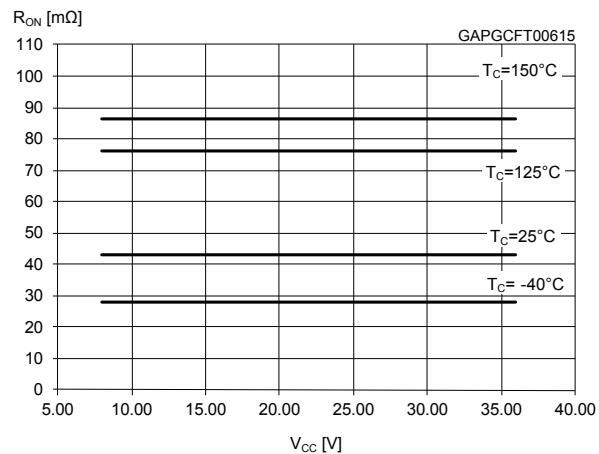
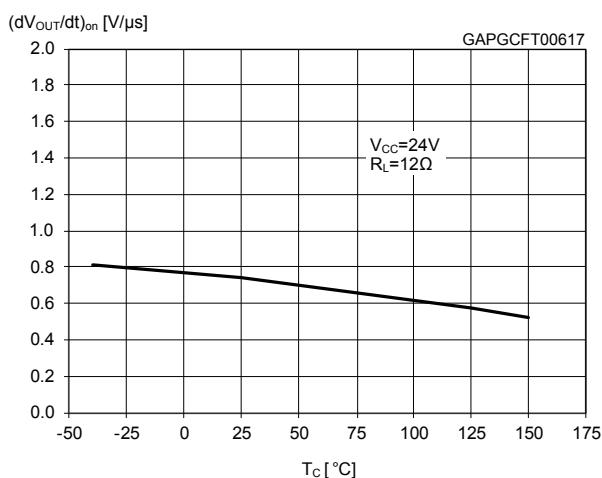
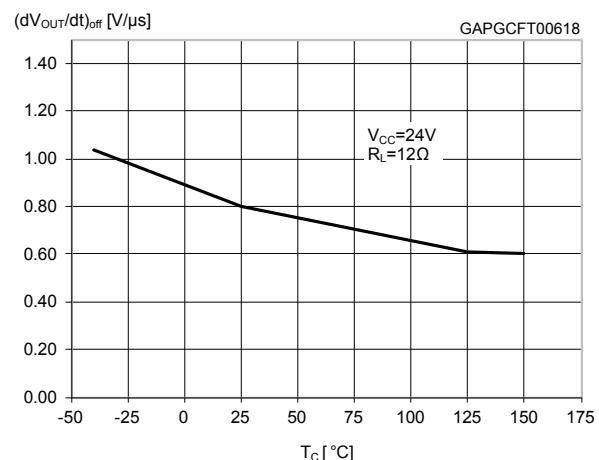
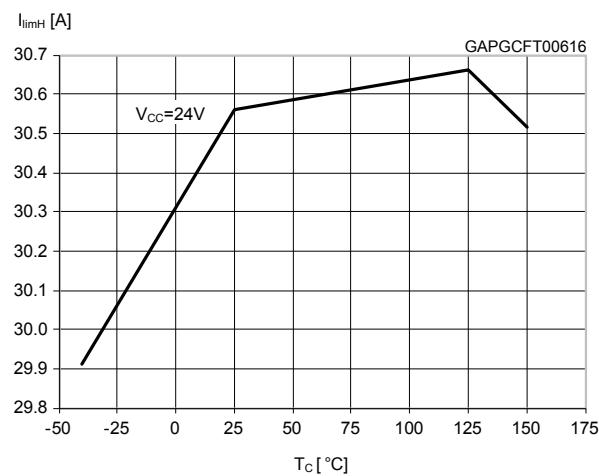
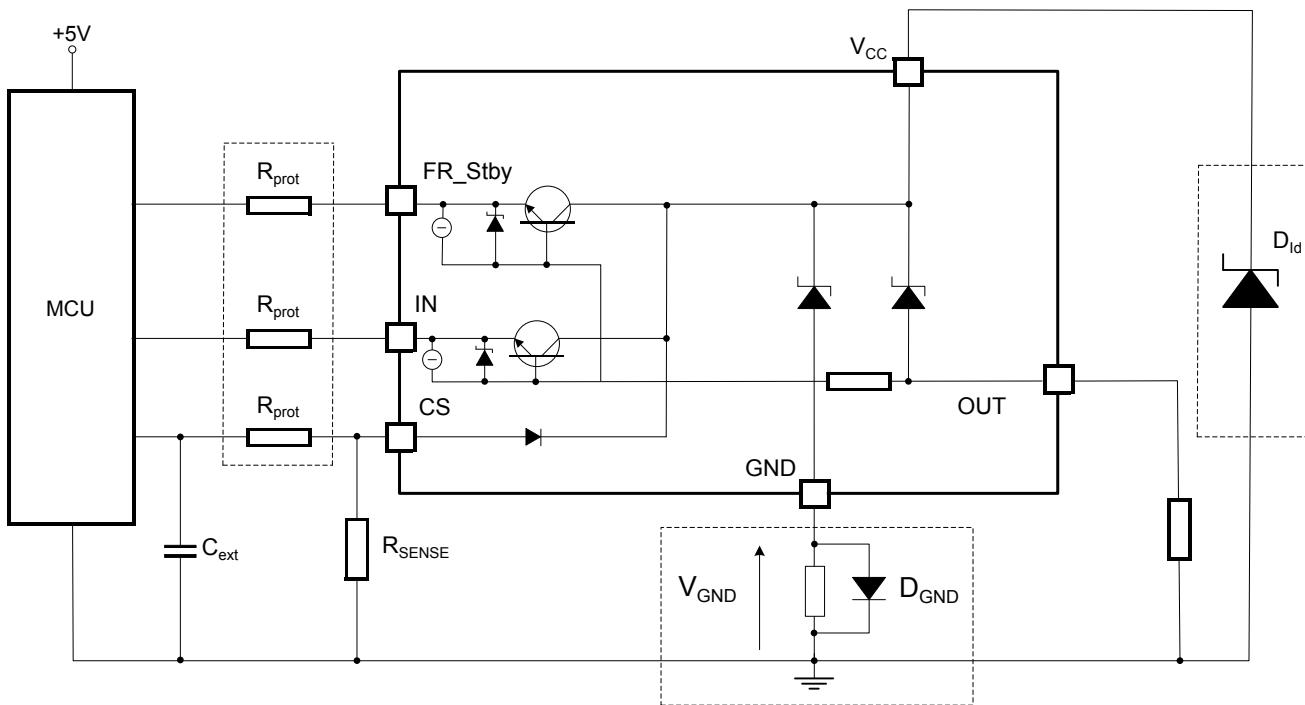
Figure 13. Off-state output current

Figure 14. High level input current

Figure 15. Input clamp voltage

Figure 16. Low level input voltage

Figure 17. High level input voltage

Figure 18. Input hysteresis voltage


Figure 19. On-state resistance vs T_c

Figure 20. On-state resistance vs V_{CC}

Figure 21. Turn-on voltage slope

Figure 22. Turn-off voltage slope

Figure 23. I_{LIMH} vs T_c


3 Application information

Figure 24. Application schematic



GAPGCFT000119

3.1 GND protection network against reverse battery

3.1.1 Solution 1: resistor in the ground line (R_{GND} only)

This solution can be used with any load type.

The following is an indication on how to dimension the R_{GND} resistor.

1. $R_{GND} \leq 600 \text{ mV} / (I_{S(on)\max.})$
2. $R_{GND} \geq (-V_{CC}) / (-I_{GND})$

Where $-I_{GND}$ is the DC reverse ground pin current and can be found in the absolute maximum rating section of the device datasheet.

Power dissipation in R_{GND} (when $V_{CC} < 0 \text{ V}$: during reverse battery situations) is:

$$P_D = (-V_{CC})^2 / R_{GND}$$

This resistor can be shared among several different HSDs. Please note that the value of this resistor should be calculated with formula (1) where $I_{S(on)\max.}$ becomes the sum of the maximum on-state currents of the different devices.

Please note that if the microprocessor ground is not shared by the device ground then the R_{GND} produces a shift ($I_{S(on)\max.} * R_{GND}$) in the input thresholds and the status output values. This shift varies depending on how many devices are ON in the case of several high side drivers sharing the same R_{GND} .

If the calculated power dissipation leads to a large resistor or several devices have to share the same resistor, then ST suggests solution 2 is used (see below).

3.1.2 Solution 2: diode (D_{GND}) in the ground line

A resistor ($R_{GND} = 4.7 \text{ k}\Omega$) should be inserted in parallel to D_{GND} if the device drives an inductive load.

This small signal diode can be safely shared amongst several different HSDs. Also in this case, the presence of the ground network produces a shift ($\approx 600 \text{ mV}$) in the input threshold and in the status output values, if the microprocessor ground is not common to the device ground. This shift does not vary if more than one HSD shares the same diode/resistor network.

3.2 Load dump protection

D_{ld} is necessary (voltage transient suppressor) if the load dump peak voltage exceeds the V_{CC} maximum DC rating. The same applies if the device is subject to transients on the V_{CC} line that are greater than the ones shown in the ISO 7637-2 2004 (E) Table 12, Table 13 and Table 14.

3.3 MCU I/Os protection

If a ground protection network is used and negative transient is present on the V_{CC} line, the control pins are pulled negative. ST suggests that a resistor (R_{prot}) has to be inserted in line to prevent the microcontroller I/Os pins from latching-up.

The value of these resistors is a compromise between the leakage current of the microcontroller and the current required by the HSD I/Os (Input levels compatibility) with the latch-up limit of microcontroller I/Os.

Equation: R_{prot} range calculation

$$-V_{CCpeak}/I_{latchup} \leq R_{prot} \leq (V_{OH\mu C} - V_{IH} - V_{GND}) / I_{IHmax}$$

Calculation example:

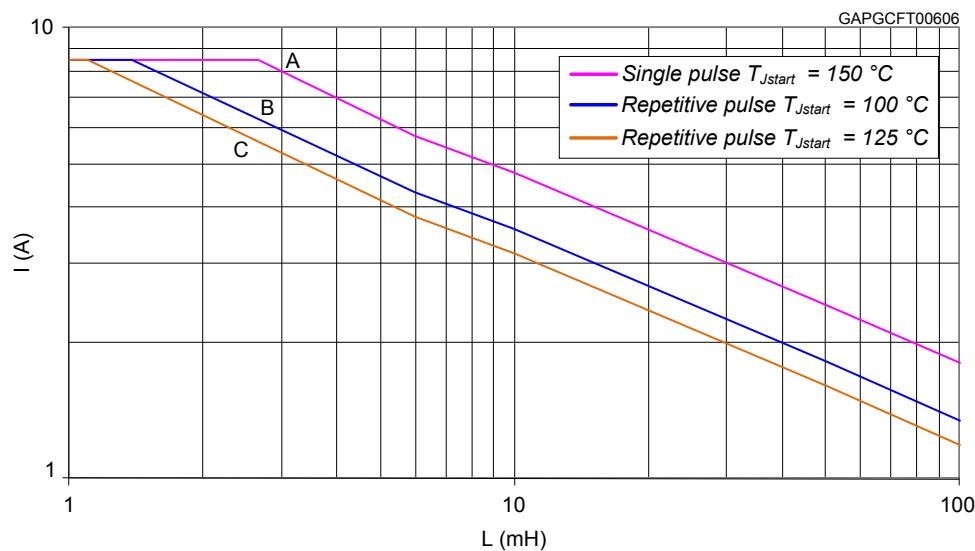
For $V_{CCpeak} = -600 \text{ V}$ and $I_{latchup} \geq 20 \text{ mA}$; $V_{OH\mu C} \geq 4.5 \text{ V}$

$$30 \text{ k}\Omega \leq R_{prot} \leq 180 \text{ k}\Omega.$$

Recommended value: $R_{prot} = 60 \text{ k}\Omega$.

4 Maximum demagnetization energy (V_{CC} = 24 V)

Figure 25. Maximum turn off current versus inductance

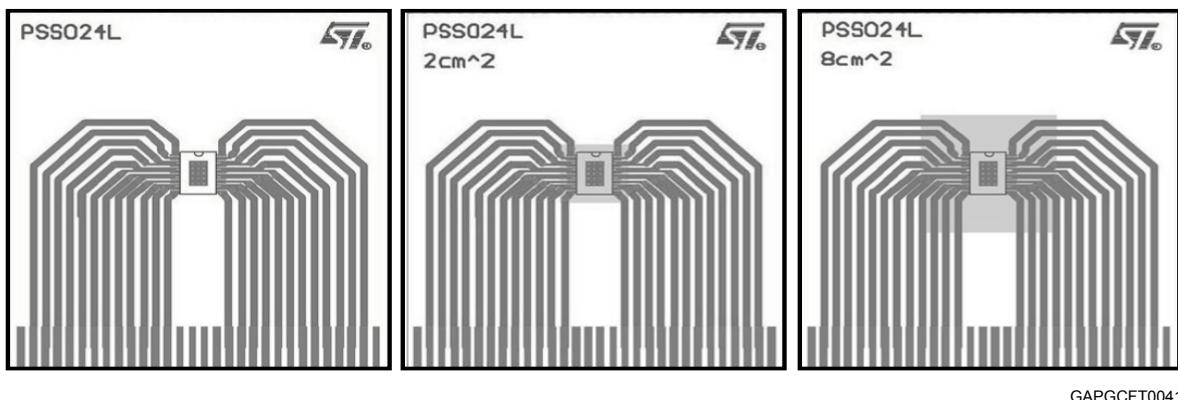


Note: Values are generated with $R_L = 0 \Omega$. In case of repetitive pulses, T_{Jstart} (at the beginning of each demagnetization) of every pulse must not exceed the temperature specified above for curves A and B.

5 Package and PCB thermal data

5.1 PowerSSO-24 thermal data

Figure 26. PowerSSO-24 PCB



GAPGCFT00418

Layout condition of R_{th} and Z_{th} measurements (PCB: double layer, thermal vias, FR4 area = 77 mm x 86 mm, PCB thickness = 1.6 mm, Cu thickness = 70 μ m (front and back side), copper areas: from minimum pad lay-out to 8 cm^2).

Figure 27. R_{thJA} vs PCB copper area in open box free air condition (one channel ON)

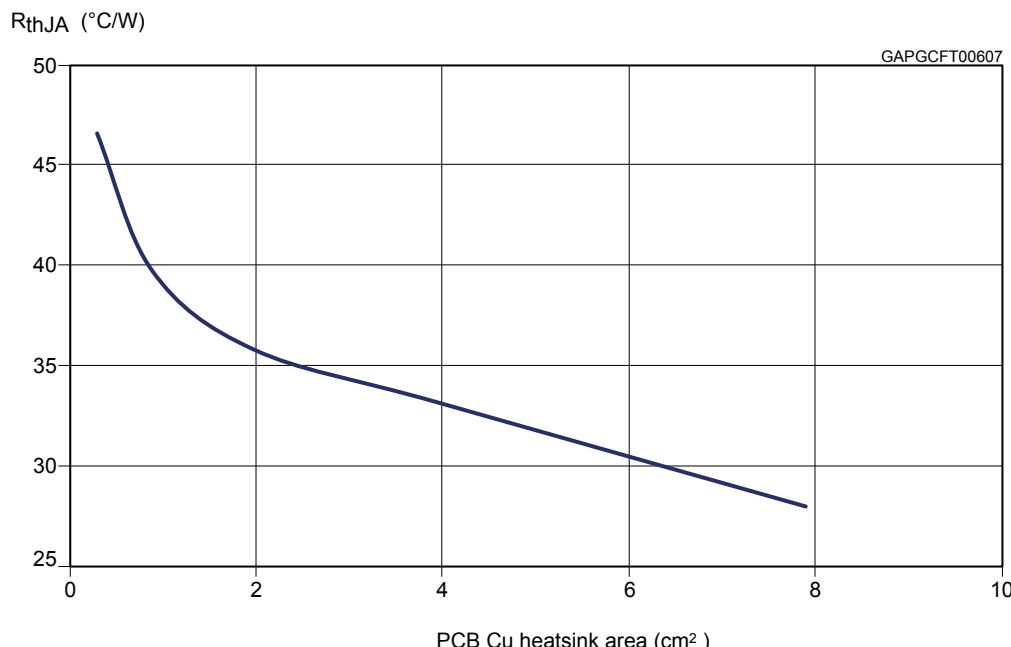


Figure 28. PowerSSO-24 thermal impedance junction ambient single pulse (one channel ON)

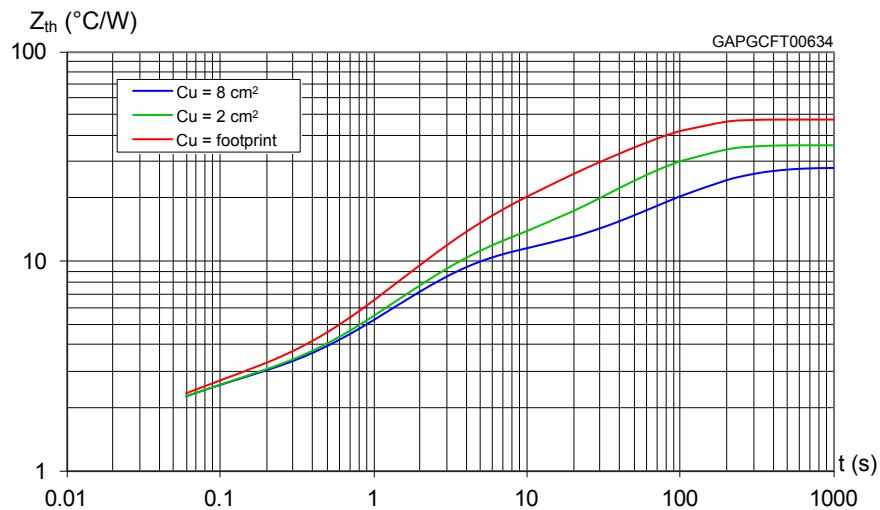
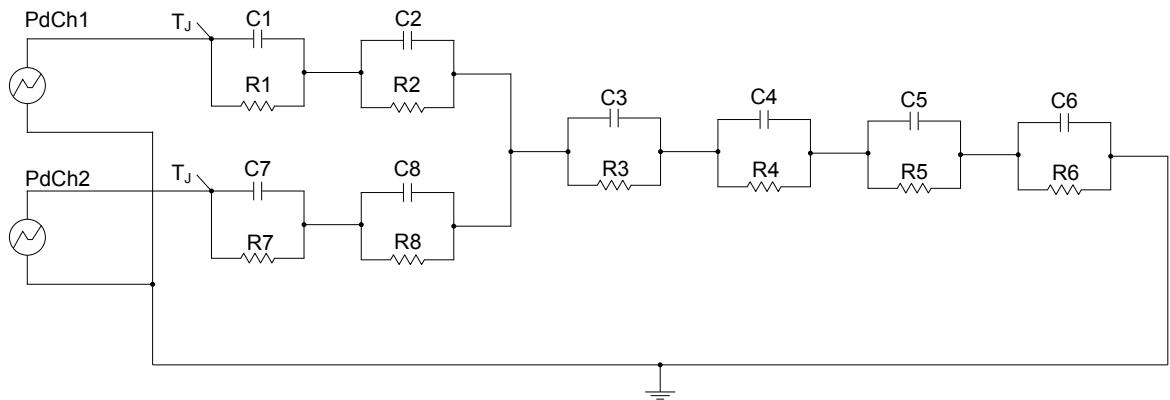


Figure 29. Thermal fitting model of a double channel HSD in PowerSSO-24



GAPGCFT00438

The fitting model is a simplified thermal tool and is valid for transient evolutions where the embedded protections (power limitation or thermal cycling during thermal shutdown) are not triggered.

Equation: pulse calculation formula

$$Z_{th\delta} = R_{th} \cdot \delta + Z_{th\text{tp}} (1 - \delta)$$

where $\delta = t_p/T$

Table 15. Thermal parameters

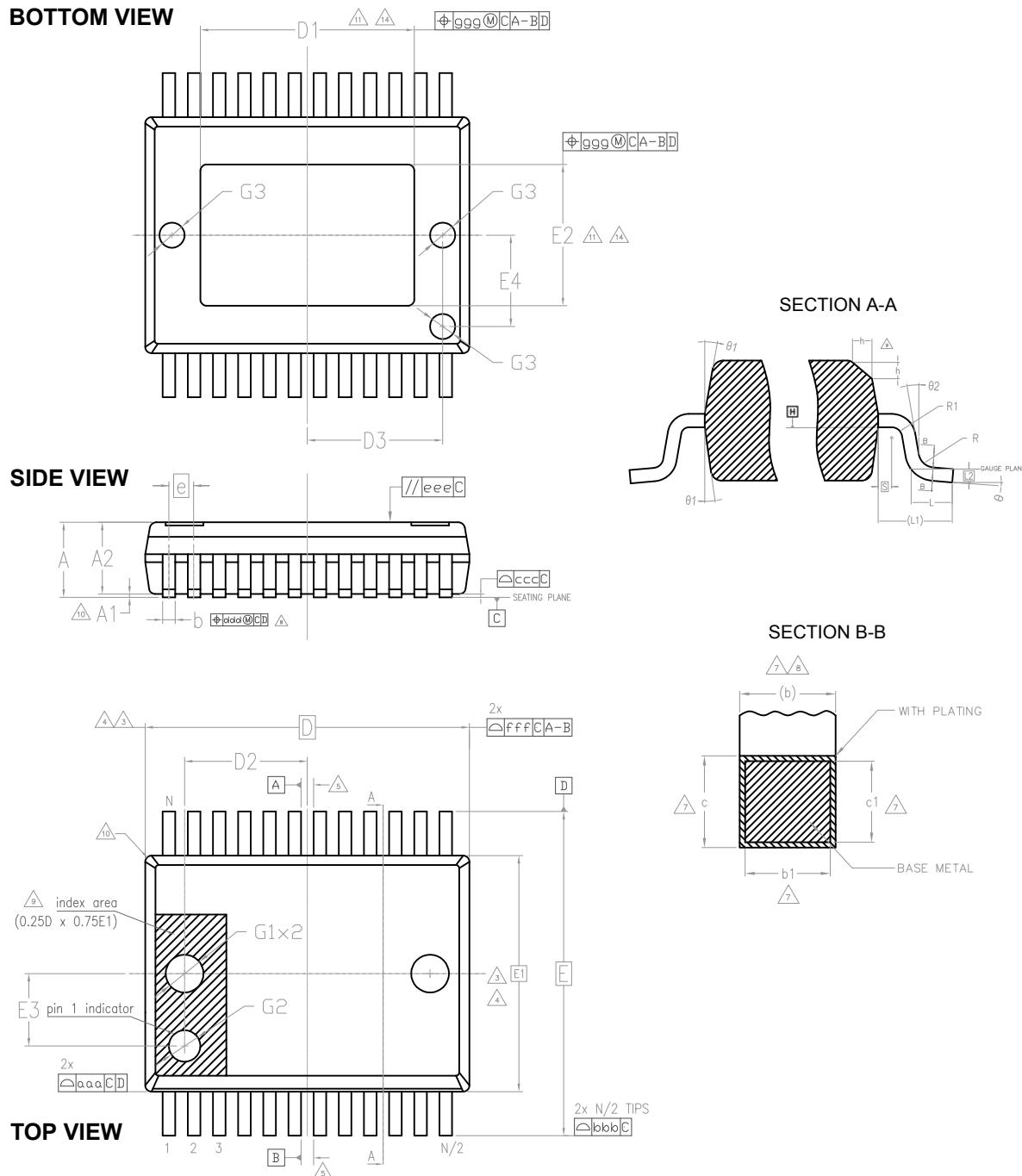
Area/island (cm ²)	Footprint	2	8
R1 = R7 (°C/W)	0.6		
R2 = R8 (°C/W)	0.75		
R3 (°C/W)	1		
R4 (°C/W)	7.7		
R5 (°C/W)	9	9	8
R6 (°C/W)	28	17	10
C1 = C7 (W.s/°C)	0.005		
C2 = C8 (W.s/°C)	0.01		
C3 (W.s/°C)	0.05		
C4 (W.s/°C)	0.3		
C5 (W.s/°C)	1	4	9
C6 (W.s/°C)	2.2	5	17

6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

6.1 PowerSSO-24 package information

Figure 30. PowerSSO-24 package dimensions



7412818_14

Table 16. PowerSSO-24 mechanical data

Symbol	Millimeters		
	Min.	Typ.	Max.
θ	0°		8°
θ1	5°		10°
θ2	0°		
A			2.45
A1	0.00		0.10
A2	2.15		2.35
b	0.33		0.51
b1	0.28	0.40	0.48
c	0.23		0.32
c1	0.20	0.20	0.30
D	10.30 BSC		
D1	6.50		7.10
D2		3.65	
D3		4.30	
e	0.80 BSC		
E	10.30 BSC		
E1	7.50 BSC		
E2	4.10		4.70
E3		2.30	
E4		2.90	
G1		1.20	
G2		1.00	
G3		0.80	
h	0.30		0.40
L	0.55	0.70	0.85
L1	1.40 REF		
L2	0.25 BSC		
N	24		
R	0.30		
R1	0.20		
S	0.25		

Table 17. PowerSSO-24 tolerance of form and position

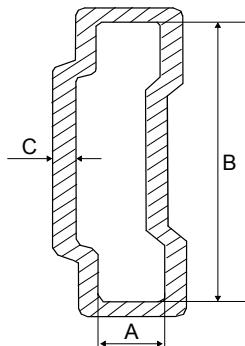
Symbol	Millimeters
aaa	0.20
bbb	0.20
ccc	0.10
ddd	0.20



Symbol	Millimeters
eee	0.10
fff	0.20
ggg	0.15

6.2 PowerSSO-24 packing information

Figure 31. PowerSSO-24 tube shipment (no suffix)

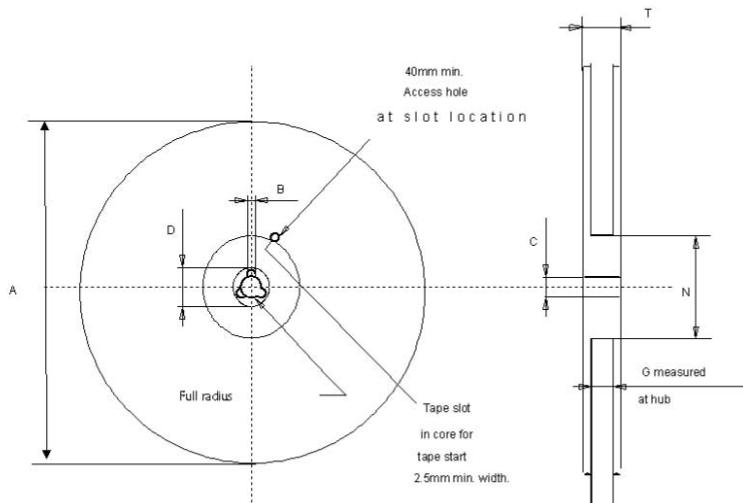


Base Q.ty	49
Bulk Q.ty	1225
Tube length (± 0.5)	532
A	3.5
B	13.8
C (± 0.1)	0.6

All dimensions are in mm.

GAPGCFT00002

Figure 32. PowerSSO-24 tape and reel shipment (suffix "TR")



Reel dimensions

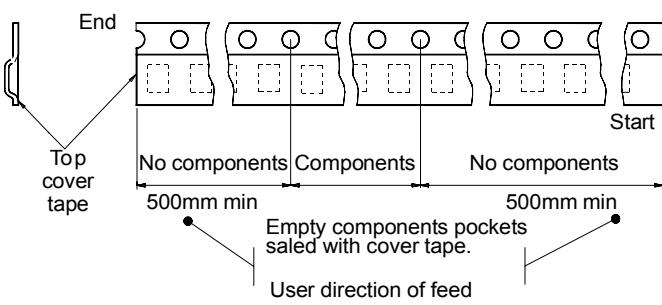
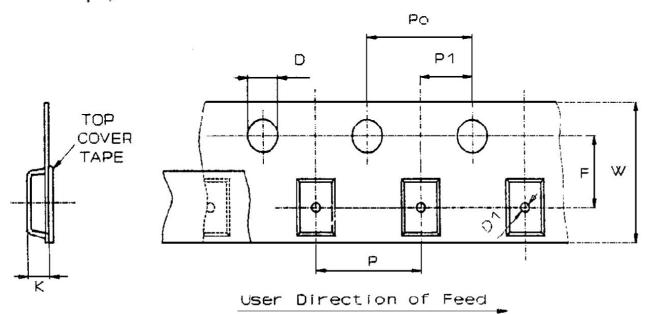
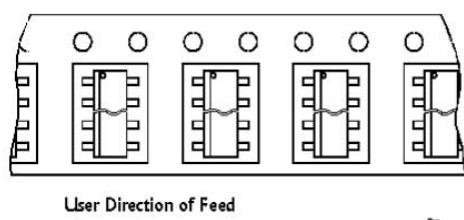
Base Q.ty	1000
Bulk Q.ty	1000
A (max)	330
B (min)	1.5
C (± 0.2)	13
F	20.2
G (+2/-0)	24.4
N (min)	100
T(max)	30.4

Tape dimension

According to Electronic Industries Association (EIA) Standard 481 rev. A, Feb 1986

Tape width	W	24
Tape hole spacing	P0 (± 0.1)	4
Component spacing	P	12
Hole diameter	D (± 0.05)	1.55
Hole diameter	D1 (min)	1.5
Hole position	F (± 0.1)	11.5
Compartment depth	K(max)	2.85
Hole spacing	P1 (± 0.1)	2

All dimensions are in mm.



GAPGCFT00421

Revision history

Table 18. Document revision history

Date	Revision	Changes
07-Feb-2012	1	Initial release.
30-Mar-2012	2	Updated <i>Table 2: Suggested connections for unused and not connected pins.</i> <i>Table 9: Current sense (8 V < V_{CC} < 36 V):</i> – dK ₀ /K ₀ : updated test condition from I _{OUT} = 100 A to I _{OUT} = 100 mA <i>Table 13: Electrical transient requirements (part 2):</i> – added note
18-Sep-2013	3	Updated Disclaimer.
24-Feb-2016	4	<i>Table 4: Thermal data:</i> – R _{thj-case} : updated value Updated <i>Section 5.1: PowerSSO-24 mechanical data</i>
17-May-2022	5	Updated PowerSSO-24 cover image Updated <i>Table 5. Power section.</i> Updated notes in <i>Table 12. Electrical transient requirements (part 1)</i> Moved <i>Section 3.4: Maximum demagnetization energy (V_{CC} = 24 V)</i> to <i>Section 4 Maximum demagnetization energy (V_{CC} = 24 V)</i> Updated <i>Section 6.1 PowerSSO-24 package information.</i> Minor text changes.

Contents

1	Block diagram and pin description	3
2	Electrical specification	5
2.1	Absolute maximum ratings	5
2.2	Thermal data	6
2.3	Electrical characteristics	6
2.4	Electrical characteristics (curves)	15
3	Application information	17
3.1	GND protection network against reverse battery	17
3.1.1	Solution 1: resistor in the ground line (R_{GND} only)	17
3.1.2	Solution 2: diode (D_{GND}) in the ground line	18
3.2	Load dump protection	18
3.3	MCU I/Os protection	18
4	Maximum demagnetization energy ($V_{CC} = 24\text{ V}$)	19
5	Package and PCB thermal data	20
5.1	PowerSSO-24 thermal data	20
6	Package information	23
6.1	PowerSSO-24 package information	23
6.2	PowerSSO-24 packing information	26
	Revision history	27

List of tables

Table 1.	Pin function	3
Table 2.	Suggested connections for unused and not connected pins	4
Table 3.	Absolute maximum ratings	5
Table 4.	Thermal data	6
Table 5.	Power section	6
Table 6.	Switching ($V_{CC} = 24\text{ V}$, $T_J = 25\text{ }^{\circ}\text{C}$)	7
Table 7.	Logic inputs	7
Table 8.	Protections and diagnostics	8
Table 9.	Current sense ($8\text{ V} < V_{CC} < 36\text{ V}$)	9
Table 10.	Openload detection ($V_{FR_Stby} = 5\text{ V}$)	10
Table 11.	Truth table	13
Table 12.	Electrical transient requirements (part 1)	14
Table 13.	Electrical transient requirements (part 2)	14
Table 14.	Electrical transient requirements (part 3)	14
Table 15.	Thermal parameters	22
Table 16.	PowerSSO-24 mechanical data	24
Table 17.	PowerSSO-24 tolerance of form and position	24
Table 18.	Document revision history	27

List of figures

Figure 1.	Block diagram	3
Figure 2.	Configuration diagram PowerSSO-24 (top view)	4
Figure 3.	Current and voltage conventions	5
Figure 4.	t_{reset} definition	8
Figure 5.	t_{stby} definition	8
Figure 6.	Current sense delay characteristics	10
Figure 7.	Openload off-state delay timing	10
Figure 8.	Switching characteristics	11
Figure 9.	Output stuck to V_{CC} detection delay time at FR_Stby activation	11
Figure 10.	Delay response time between rising edge of output current and rising edge of current sense	12
Figure 11.	Output voltage drop limitation	12
Figure 12.	Device behavior in overload condition	13
Figure 13.	Off-state output current	15
Figure 14.	High level input current	15
Figure 15.	Input clamp voltage	15
Figure 16.	Low level input voltage	15
Figure 17.	High level input voltage	15
Figure 18.	Input hysteresis voltage	15
Figure 19.	On-state resistance vs T_C	16
Figure 20.	On-state resistance vs V_{CC}	16
Figure 21.	Turn-on voltage slope	16
Figure 22.	Turn-off voltage slope	16
Figure 23.	I_{LIMH} vs T_C	16
Figure 24.	Application schematic	17
Figure 25.	Maximum turn off current versus inductance	19
Figure 26.	PowerSSO-24 PCB	20
Figure 27.	R_{thJA} vs PCB copper area in open box free air condition (one channel ON)	20
Figure 28.	PowerSSO-24 thermal impedance junction ambient single pulse (one channel ON)	21
Figure 29.	Thermal fitting model of a double channel HSD in PowerSSO-24	21
Figure 30.	PowerSSO-24 package dimensions	23
Figure 31.	PowerSSO-24 tube shipment (no suffix)	26
Figure 32.	PowerSSO-24 tape and reel shipment (suffix "TR")	26

IMPORTANT NOTICE – READ CAREFULLY

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgment.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. For additional information about ST trademarks, refer to www.st.com/trademarks. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2022 STMicroelectronics – All rights reserved

单击下面可查看定价，库存，交付和生命周期等信息

[>>STMicro\(意法半导体\)](#)